

First Hit

Generate Collection

Print

L1: Entry 2 of 36

File: JPAB

Aug 9, 2002

PUB-NO: JP02002222871A
DOCUMENT-IDENTIFIER: JP 2002222871 A
TITLE: METHOD FOR HEAT TREATMENT

PUBN-DATE: August 9, 2002

INVENTOR-INFORMATION:

NAME

COUNTRY

KATO, HISASHI

NISHIDA, TATSUO

TOJO, YUKIO

ASSIGNEE-INFORMATION:

NAME

COUNTRY

TOKYO ELECTRON LTD

APPL-NO: JP2001356595

APPL-DATE: November 21, 2001

PRIORITY-DATA: 2000JP-356728 (November 22, 2000)

INT-CL (IPC): H01 L 21/8242; H01 L 21/205; H01 L 27/108

ABSTRACT:

PROBLEM TO BE SOLVED: To provide a method for heat treatment which can reduce a facility cost and can improve throughput and characteristics.

SOLUTION: When forming, for example, the surface of a lower electrode for a capacitor on the surface of a semiconductor wafer W which is an object to be processed, a process of depositing a HSG polysilicon film (rugged polysilicon film) 16 non-selectively and a process of doping an impurity such as phosphorus into the polysilicon film are conducted continuously in one and the same processing container 28. As a result, the facility cost can be reduced and throughput can be increased.

COPYRIGHT: (C)2002, JPO

BEST AVAILABLE COPY